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			U.S.	. PATENT	DOCUMENTS				
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		3,602,841	8-31-71	McGro	ddy	<u> </u>			
		4,665,415	5-12-87	Esaki,	et al.	<u> </u>			
		4,853,076	8-1-89	Tsaur,	et al.				
-		4,855,245	8-8-89	Neppl,	et al.				
		4,952,524	8-28-90	Lee, et	al.				
			U.S. PATENT	CAPPLICA	ATION PUBLICATIONS	······································			
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		US 2001/0009784 A1	7-26-01	Ma, et	al.				
		US 2002/0063292 A1	5-30-02	Armstr	rong, et al.				
		US 2002/0074598 A1	6-20-02	Doyle,	et al.				
		US 2002/0086472	7-4-02	Roberd	is, et al.				
			FORE	IGN PATE	ENT DOCUMENTS				
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		JP64-76755	03-1989	Japan					
									
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		Kern Rim, et al., "Trai Devices Meeting, 26, 8,	nsconductance En 1, IEEE, Septem	hancemer ber 1998.	nt in Deep Submicron Strai	ned-Si n-M	OSFETs". Inter	national Ele	ctron
		Kern Rim, et al., "Cha VLSI Technology Dige	racteristics and D st of Technical Pa	evice Des pers, IEE	ign of Sub-100 nm Strained E, pp. 98-99.	Si N- and	PMOSFETs." 2	002 Sympos	lum o
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		4,958,213	9-18-90	Eklund	d, et al.				
		5,006,913	4-9-91	Sugah	ara, et al.				
		5,060,030	10-22-91	Hoke,	et al.				
		5,081,513	1-14-92	Jackson, et al.					
		5,108,843	4-28-92	Ohtak	a, et al.			<u></u>	
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		US 2002/0086497 A1	7-4-02	Kwok					
	US 2002/0090791 A1 7-11-02 Do		Doyle,	et al.					
		US 2003/0032261 A1	2-13-03 Yeh,		t al.				
		US 2003/0040158 A1	2-27-03	Saitoh					
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		Crosser Scott et al. "		DOCUME			Pertinent Pages, Ed and Trench Isolati		Stress
		International Electron	Devices Meeting,	34.4.1, I	luction Caused by Transist EEE, September 1999.	,			
		F. Ootsuka, et al., "A I Application." Internat	lighly Dense, Hig ional Electron De	h-Perfor evices Me	mance 130nm Node CMOS eting, 23.5.1, IEEE, April 2	Technology 2000.	for Large Scale	System-on	-a-Chip
EXAMIN	ER				DATE CONSIDERED				
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	· · · ·		U	.s. paten	DOCUMENTS			
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	FILING DATE
		5,134,085	7-28-92	Gilgen	, et al.			
-		5,310,446	5-10-94	Konisi	ni, et aL			
		5,354,695	10-11-94	Leedy				
								

U.S. PATENT APPLICATION PUBLICATIONS

Hsu, et al.

Burroughes, et al.

12-6-94

2-21-95

5,371,399

5,391,510

•EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE NAME		CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		US 2003/0057184 A1	3-27-03	Yu, et al.			
	-	US 2003/0067035 A1	4-10-03	Tews, et al.			
							
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FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.

A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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· · · · ·			U.S	. PATENT	DOCUMENTS				
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		5,459,346	10-17-95	Asakav	va, et al.				
		5,471,948	12-5-95	Burrou	ighes, et al.				
		5,557,122	9-17-96	Shriva	stava, et al.		·		
		5,561,302	10-1-96	Cande	laria			***************************************	
		5,565,697	10-15-96	Asaka	Asakawa, et al.				
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-		K. Ota, et al., "Novel I Devices Meeting, 2.2.1,	ocally Strained (, IEEE, February	Channel T 2002.	echnique for High Perform	ance 55nm	CMOS." Intern	ational Ele	ectron
		G. Zhang, et al., "A Ne IEEE Transactions on	ew 'Mixed-Mode' Electron Devices	Reliabilit , vol. 49, i	y Degradation Mechanism 10. 12, December 2002, pp. 2	In Advance 2151-56.	d Si and SiGe Bi	polar Tran	sistors.
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.

C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		5,683,934	11-4-97	Candel	aria				
**		5,840,593	11-24-98	Leedy					
		5,861,651	1-19-99	Brasen	, et al.				
		5,880,040	3-9-99	Sun, et	al.				
		5,940,716	8-17-99	Jin, et	al.				
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	T	S.R. Sheng, et al., "Dep	gradation and Rec	covery of	SiGe HBTs Following Radi	ation and H	ot-Carrier Stres	sing." Pp. 14-15.	
		Z. Yang, et al., "Avala Transistors." Pp. 1-5.	nche Current Ind	uced Hot	Carrier Degradation in 200	GHz SiGe	Heterojunction	Bipolar	
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.

H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		6,117,722	9-12-00	Wuu, e	t al.				
		6,133,071	10-17-00	Nagai					
		6,165,383	12-26-00	Chou					
		6,221,735	4-24-01	Manle	y, et al.				
		6,228,694	5-8-01	Doyle,	et al.				
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		6,246,095	6-12-01	Brady,	et al.			
		6,255,169	7-3-01	Li, et a	l			
		6,261,964	7-17-01	Wu, et	al.			
		6,265,317	7-24-01	Chiu, e	t al.			
		6,274,444	8-14-01 Wang		ang			
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		6,281,532	8-28-01	Doyle,	et al.				
		6,284,623	9-4-01	Zhang,	et al.				,
		6,284,626	9-4-01	Kim					<u> </u>
		6,319,794	11-20-01	Akatsu	, et al.				
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		6,362,082	3-26-02	Doyle,	et al.				
		6,368,931	4-9-02	Kuhn,	et al.				
		6,403,486	6-11-02	Lou					
		6,403,975	6-11-02	Brunne	er, et al.				
		6,406,973	6-18-02	Lee					
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		6,461,936	10-8-02	von Eh	renwall					
		6,476,462	11-5-02	Shimiz	u, et al.					
		6,483,171	11-19-02	Forbes	, et al.					
		6,493,497	12-10-02	Ramda	ni, et al.					
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		6,501,121	12-31-02	Yu, et a	ıl.				
		6,506,652	1-14-03	Jan, et	al.				
		6,509,618	1-21-03	Jan, et	al.				
		6,521,964 2-18-03 Jan, 6			, et al.				
		6,531,369	3-11-03	Ozkan,	et al.				
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					Applicant(s) K C Filing Date 9/16/20	203	Group Art Unit 28-22		
			U.S	. PATENT	DOCUMENTS				
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		6,531,740	3-11-03	Bosco,	et al.				
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			U.S. PATENT	r applica	ATION PUBLICATIONS				
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